

ABSTRACT OF THE DISCLOSURE

The present invention provides a resist pattern thickening material which can thicken a resist pattern to be thickened regardless of a material or a size thereof so as to form a fine space pattern, exceeding an exposure limit of exposure light. The resist pattern thickening material comprises: a resin; a crosslinking agent; and a nitrogen-containing compound. In a process for forming a resist pattern of the present invention, the resist pattern thickening material is applied on a surface of a resist pattern to be thickened, thereby forming a resist pattern. A process for manufacturing a semiconductor device of the present invention includes: applying the thickening material on a surface of a resist pattern to be thickened which is formed on an underlying layer, so as to thicken the resist pattern to be thickened and form a resist pattern; and patterning the underlying layer by etching using the resist pattern.